## Lec (06)



## Summary of Diode

The bias voltage must be greater than the barrier potential.
Barrier potential: 0.7 V for silicon.
Majority carriers provide the forward current.
The depletion region narrows.


The bias voltage must be less than the breakdown voltage.
There is no majority carrier current after transition time.
Minority carriers provide a negligibly small reverse current.
The depletion region widens.


## Example 1

An ac voltage of peak value 20 V is connected in series with a silicon diode and load resistance of $500 \Omega$. If the forward resistance of the diode is $10 \Omega$, find:
(a) peak current through the diode
(b) peak output voltage.


What will be these values if the diode is considered as an ideal diode?

Solution. The diode will conduct during the positive half-cycles of ac input voltage. The equivalent circuit is
(a) peak current through the diode
$V_{F}=V_{P B}+\left(l_{f}\right)_{\text {peak }}\left[r_{f}+R_{L}\right]$
$\left(I_{f}\right)_{\text {peak }}=\frac{V_{F}-V_{P B}}{r_{f}+R_{L}}=\frac{20-0.7}{10+500}=37.8 \mathrm{~mA}$

## (b) peak output voltage

$V_{\text {out }}=\left(I_{f}\right)_{\text {peak }} \times R_{L}=37.8 \times 10^{-3} \mathrm{~A} \times 500 \Omega=18.9 \mathrm{~V}$


For an ideal diode $\mathrm{V}_{\mathrm{PB}}=\mathbf{0}$ and $\mathrm{r}_{\mathrm{f}}=\mathbf{0}$
$\left(I_{f}\right)_{\text {peak }}=\frac{V_{F}}{R_{L}}=\frac{20}{500}=40 \mathrm{~mA} \quad \& \quad V_{\text {out }}=\left(I_{f}\right)_{\text {peak }} \times R_{L}=40 \times 10^{-3} \mathrm{~A} \times 500 \Omega=20 \mathrm{~V}$

## Example 2

Calculate the current through $48 \Omega$ resistor in the circuit shown in the Figure (i). Assume the diodes to be of silicon and forward resistance of each diode is $1 \Omega$.

Diodes $D_{1}$ and $D_{3}$ are forward biased while diodes $D_{2}$ and $D_{4}$ are reverse biased. We can, therefore, consider the branches containing diodes $D_{2}$ and $D_{4}$ as "open".
Replacing diodes $D_{1}$ and $D_{3}$ by their equivalent circuits and making the branches containing diodes $D_{2}$ and $D_{4}$ open,


We get the circuit shown in the Figure. Note that for a silicon diode, the barrier voltage is 0.7 V .


Net circuit voltage $=10-0.7-0.7=8.6 \mathrm{~V}$
Total circuit resistance $=1+48+1=50 \Omega$
Circuit current $=8.6 / 50=0.172 \mathrm{~A}=172 \mathrm{~mA}$

## Example 3

Determine the current I in the circuit shown in the Figure. Assume the diodes to be of silicon and forward resistance of diodes to be zero.


Solution. The conditions of the problem suggest that diode $D_{1}$ is forward biased and diode $D_{2}$ is reverse biased. We can, therefore, consider the branch containing diode $D_{2}$ as open. Further, diode $D_{1}$ can be replaced by its simplified equivalent circuit.

$$
I=\frac{E_{1}-E_{2}-V_{0}}{R}=\frac{24-4-0.7}{2 \mathrm{k} \Omega}=\frac{19.3 \mathrm{~V}}{2 \mathrm{k} \Omega}=9.65 \mathrm{~mA}
$$

## Example 4

Find $V_{Q}$ and $I_{D}$ in the network shown. Use practical model.

Solution. By symmetry, current in each branch is $I_{D}$ so that current in branch $C D$ is $2 I_{D}$.
Applying Kirchhoff's voltage law to the closed circuit $A B C D A$, we have,

$$
\begin{aligned}
& -0.7-I_{D} \times 2-2 I_{D} \times 2+10=0 \\
& 6 I_{D}=9.3 \\
& I_{D}=\frac{9.3}{6}=1.55 \mathrm{~mA}
\end{aligned}
$$



$$
V_{Q}=\left(2 I_{D}\right) \times 2 \mathrm{k} \Omega=(2 \times 1.55 \mathrm{~mA}) \times 2 \mathrm{k} \Omega=6.2 \mathrm{~V}
$$

## Example 5

Determine current through each diode in the circuit shown. Use practical model. Assume diodes to be similar.

Solution. The applied voltage forward biases each diode so that they conduct current in the same direction.
$I_{1}=\frac{\text { Voltage across } R}{R}=\frac{15-0.7}{0.5 \mathrm{k} \Omega}=28.6 \mathrm{~mA}$
Since the diodes are similar

$$
I_{D 1}=I_{D 2}=\frac{I_{1}}{2}=\frac{28.6}{2}=14.3 \mathrm{~mA}
$$



## Example 6

Determine the currents $I_{1}, I_{2}$ and $I_{3}$ for the network shown. Use practical model for the diodes.

Solution. An inspection of the circuit shown it shows that both diodes $D_{1}$ and $D_{2}$ are forward biased.
The voltage across $R_{2}(=3.3 \mathrm{k} \Omega)$ is 0.7 V .

$$
\therefore \quad I_{2}=\frac{0.7 \mathrm{~V}}{3.3 \mathrm{k} \Omega}=0.212 \mathrm{~mA}
$$

Applying Kirchhoff's voltage law to loop ABCDA, we have, $-0.7-0.7-I_{1} R_{1}+20=0$

$$
\begin{aligned}
& I_{1}=\frac{20-0.7-0.7}{R_{1}}=\frac{18.6 \mathrm{~V}}{5.6 \mathrm{k} \Omega}=3.32 \mathrm{~mA} \\
& I_{3}=I_{1}-I_{2}=3.32-0.212=3.108 \mathrm{~mA}
\end{aligned}
$$




## Diodes and Applications

## Revision (02)

## Summary of power supply rectifiers

Rectifier type: Half-wave

Schematic diagram:


Full-wave Centre-tap


Bridge Rectifier


Typical output waveform:


| S. No. | Particulars | Half-wave | Centre-tap | Bridge type |
| :---: | :--- | :--- | :--- | :--- |
| 1 | No. of diodes | 1 | 2 | 4 |
| 2 | Transformer necessary | no | yes | no |
| 3 | Max. efficiency | $40.6 \%$ | $81.2 \%$ | $81.2 \%$ |
| 4 | Ripple factor | 1.21 | 0.48 | 0.48 |
| 5 | Output frequency | $f_{\text {in }}$ | $2 f_{\text {in }}$ | $2 f_{\text {in }}$ |
| 6 | Peak inverse voltage | $V_{m}$ | $2 V_{m}$ | $V_{m}$ |

## Example 1

An ac supply of 230 V is applied to a half-wave rectifier circuit through a transformer of turn ratio 10:1. Assume the diode to be ideal. Find
(i) the output dc voltage
(ii) the peak inverse voltage.

## Solution

Primary to secondary turns is $\mathrm{N}_{1} / \mathrm{N}_{2}=10$ rms of the primary voltage $=230 \mathrm{~V}$

$\therefore$ Max primary voltage $\mathrm{V}_{\mathrm{pm}}=\sqrt{2} \times 230=325.3 \mathrm{~V}$
$\therefore$ Max secondary voltage $\mathrm{V}_{\mathrm{sm}}=\mathrm{V}_{\mathrm{pm}} \times\left(\mathrm{N}_{2} / \mathrm{N}_{1}\right)=325.3 \times(1 / 10)=32.53 \mathrm{~V}$
(i) the output dc voltage

$$
\begin{aligned}
I_{d . c .} & =\frac{I_{m}}{\pi} \\
V_{d c} & =\frac{I_{m}}{\pi} \times R_{L} \\
& =\frac{V_{s m}}{\pi} \\
& =\frac{32.53}{\pi}=10.36 \mathrm{~V}
\end{aligned}
$$


(ii) the peak inverse voltage.

The maximum secondary voltage appears across the diode.
$\therefore$ Peak inverse voltage $\mathrm{V}_{\mathrm{sm}}=32.53 \mathrm{~V}$

## Example 2

A half-wave rectifier is used to supply 50 V dc to a resistive load of $800 \Omega$. The diode has a resistance of $25 \Omega$. Calculate ac voltage required.

## Solution

Output dc voltage, $V_{d c}=50 \mathrm{~V}$
Diode resistance, $r_{f}=25 \Omega$
Load resistance, $R_{L}=800 \Omega$
Let $V_{m}$ be the maximum value of ac voltage required.

$$
\begin{aligned}
\therefore V_{d c} & =I_{d c} \times R_{L} \\
V_{d c} & =\frac{I_{m}}{\pi} \times R_{L}
\end{aligned}
$$

$$
\begin{aligned}
& {\left[\because I_{m}=\frac{V_{m}}{r_{f}+R_{L}}\right]} \\
& V_{d c}=\frac{V_{m}}{\pi\left(r_{f}+R_{L}\right)} \times R_{L} \\
& 50=\frac{V_{m}}{\pi(25+800)} \times 800 \\
& V_{m}=\frac{\pi \times 825 \times 50}{800}=162 \mathrm{~V}
\end{aligned}
$$

Hence, ac voltage of maximum value 162 V is required.

## Example 3

A full-wave rectifier uses two diodes, the internal resistance of each diode may be assumed constant at $20 \Omega$. The transformer rms secondary voltage from center tap to each end of secondary is 50 V and load resistance is $980 \Omega$. Find:
(i) the average load current, (ii) the rms value of load current

## Solution

Max. ac voltage $\quad V_{m}=50 \times \sqrt{2}=70.7 \mathrm{~V}$
Max. load current $I_{m}=\frac{V_{m}}{r_{f}+R_{L}}=\frac{70.7 \mathrm{~V}}{(20+980) \Omega}=70.7 \mathrm{~mA}$
(i) average load current

$$
I_{d c}=\frac{2 I_{m}}{\pi}=\frac{2 \times 70.7}{\pi}=45 \mathrm{~mA}
$$

(ii) RMS value of load current is

$$
I_{r m s}=\frac{I_{m}}{\sqrt{2}}=\frac{70.7}{\sqrt{2}} \overleftrightarrow{A B}=50 \mathrm{~mA}
$$

## Example 4

In the center-tap circuit shown, the diodes are assumed to be ideal i.e. having zero internal resistance. Find: (i) dc output voltage (ii) peak inverse voltage.

## Solution

Primary to secondary turns, $N_{1} / N_{2}=5$
RMS primary voltage $=230 \mathrm{~V}$
$\therefore$ RMS secondary voltage $=230 \times(1 / 5)=46 \mathrm{~V}$


Maximum voltage across secondary $=46 \times \sqrt{2}=65 \mathrm{~V}$
Maximum voltage across half secondary winding is $V_{m}=65 / 2=32.5 \mathrm{~V}$

## (i) dc output voltage

$$
\begin{gathered}
V_{\mathrm{AVG}}=\frac{2 \mathrm{~V}_{\mathrm{m}}}{\pi} \\
V_{d c}=V_{\text {AVG }}=2 \times 32.5 / 3.14=20.7 \mathrm{~V}
\end{gathered}
$$

## (ii) peak inverse voltage.

The peak inverse voltage is equal to maximum secondary voltage, i.e.


$$
\text { PIV }=65 \mathrm{~V}
$$

## Example 5

In the bridge type circuit shown, the diodes are assumed to be ideal. Assume primary to secondary turns to be 4 . Find:
(i) dc output voltage
(ii) peak inverse voltage
(iii) output frequency.


## Solution

Primary/secondary turns, $N_{1} / N_{2}=4$
RMS primary voltage $=230 \mathrm{~V}$
$\therefore$ RMS secondary voltage $=230\left(N_{2} / N_{1}\right)=230 \times(1 / 4)=57.5 \mathrm{~V}$
Maximum voltage across secondary is
$V_{m}=57.5 \times \sqrt{2}=81.3 \mathrm{~V}$
Average output voltage, $V_{\mathrm{AVG}}=\frac{2 \mathrm{~V}_{\mathrm{m}}}{\pi}$
(i) $\therefore$ dc output voltage, $\mathrm{V}_{\mathrm{dc}}=\mathrm{V}_{\mathrm{AVG}}=2 \times 81.3 / 3.14=52 \mathrm{~V}$
(ii) peak inverse voltage (PIV $=81.3 \mathrm{~V}$ )
(iii) In full wave rectification, there are two output pulses for each complete cycle of the input ac voltage. Therefore, the output frequency is twice that of the ac supply frequency i.e.

$$
f_{\text {out }}=2 \times f_{\text {in }}=2 \times 50=100 \mathrm{~Hz}
$$

## More problem to be solved by your self

(1) Figures show the center-tap and bridge type circuits having the same load resistance and transformer turn ratio. The primary of each is connected to $230 \mathrm{~V}, 50 \mathrm{~Hz}$ supply. Assume the diodes to be ideal. (i) Find the dc voltage in each case. (ii) PIV for each case for the same dc output.

(2) The four diodes used in a bridge rectifier circuit have forward resistances which may be considered constant at $1 \Omega$ and infinite reverse resistance. The alternating supply voltage is 240 V rms and load resistance is $480 \Omega$. Calculate (i) average load current and (ii) power dissipated in each diode.

